We claim:

1. A method for improving the wettability of a substrate, the method comprising:

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contacting the substrate with a process solution comprising: a solvent selected from the group consisting of an aqueous solvent, a non-aqueous solvent, and combinations thereof; and about 10 ppm to about 10,000 ppm of at least one surfactant having the formula (I) or (II):

$$R_3$$
 R_4
 O
 OH
 R_2
 OH

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wherein R_1 and R_4 are a straight or a branched alkyl chain having from 3 to 10 carbon atoms; R_2 and R_3 are either H or an alkyl chain having from 1 to 5 carbon atoms; and m, n, p, and q are numbers that range from 0 to 20;

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coating the substrate with a resist coating to provide a resist-coated substrate;

exposing at least a portion of the resist-coated substrate to a radiation source for a time sufficient to provide a pattern on the resist coating; and

applying an aqueous developer solution to the substrate to dissolve at least a portion of the resist coating.

2. The method of claim 1 further comprising the step of contacting the resistcoated substrate with the process solution.

- 3. The method of claim 1 wherein the process solution further comprises from about 10 to about 10,000 ppm of at least one dispersant.
- 4. The method of claim 3 wherein the at least one dispersant comprises an ionic compound.
- 5 5. The method of claim 3 wherein the at least one dispersant comprises a nonionic compound.
 - 6. The method of claim 1 wherein the value of (n + m) ranges from 0 to 30.
 - 7. The method of claim 6 wherein the value of (n + m) ranges from 1.3 to 15.
 - 8. The method of claim 1 wherein the value of (p + q) ranges from 0 to 30.
- 10 9. The method of claim 8 wherein the value of (p + q) ranges from 1 to 10.
 - The method of claim 1 wherein the process solution is formed prior to the contacting step.
 - 11. The method of claim 1 wherein the process solution is formed during the contacting step.
- 15 12. The method of claim 1 wherein the contacting step is performed before the coating step.
 - 13. The method of claim 1 wherein the contacting step is performed after the coating step.
 - 14. A method for improving the wettability of a substrate, the method comprising:

 contacting a substrate with a process solution comprising a solvent

 selected from the group consisting of an aqueous solvent, a non-aqueous solvent,

 and combinations thereof; and about 10 ppm to about 10,000 ppm of at least one

 surfactant having the formula:

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$$R_3$$
 R_2
 R_1
 R_2
 R_1
 R_2
 R_1
 R_2
 R_3
 R_4
 R_2
 R_3
 R_4
 R_4
 R_5
 R_7
 R_7
 R_7
 R_7
 R_7
 R_7
 R_8

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wherein R_1 and R_4 are a straight or a branched alkyl chain having from 3 to 10 carbon atoms; R_2 and R_3 are either H or an alkyl chain having from 1 to 5 carbon atoms; and m, n, p and q are numbers that range from 0 to 20;

coating the substrate with a resist coating to provide a resist-coated substrate;

exposing at least a portion of the resist-coated substrate to a radiation source for a time sufficient to provide a pattern on the resist coating; and

applying an aqueous developer solution to the substrate to dissolve at least a portion of the resist coating wherein the contacting step is conducted prior to the applying step.

15. A method for improving the wettability of a substrate by reducing a contact angle of an aqueous developer solution on the surface of the substrate, the method comprising:

contacting the substrate with a process solution comprising: a solvent selected from the group consisting of an aqueous solvent, a non-aqueous solvent, and combinations thereof; and about 10 ppm to about 10,000 ppm of at least one surfactant having the formula (I) or (II):

$$R_3$$
 R_4
 R_5
 R_6
 R_7
 R_8
 R_8
 R_8
 R_9
 R_9

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wherein R_1 and R_4 are a straight or a branched alkyl chain having from 3 to 10 carbon atoms; R_2 and R_3 are either H or an alkyl chain having from 1 to 5 carbon atoms; and m, n, p, and q are numbers that range from 0 to 20;

coating the substrate with a resist coating to provide a resist-coated substrate:

exposing at least a portion of the resist-coated substrate to a radiation source for a time sufficient to provide a pattern on the resist coating;

contacting the resist-coated substrate with the process solution; and applying the aqueous developer solution to the substrate to dissolve at least a portion of the resist coat wherein the first and second contacting steps are conducted prior to the applying step.

- 16. The method of claim 15 wherein contact angle of the aqueous developer solution on the surface of the resist-coated substrate is about 60° or less at 30 seconds.
- 17. The method of claim 16 wherein the contact angle of the aqueous developer solution on the surface of the resist-coated substrate is about 50° or less at 30 seconds.

- 18. The method of claim 17 wherein the contact angle of the aqueous developer solution on the surface of the resist-coated substrate is about 40° or less at 30 seconds.
- 19. A process solution, the solution comprising:

a solvent selected from the group consisting of an aqueous solvent, a non-aqueous solvent, and combinations thereof; and

about 10 to about 10,000 ppm of at least one surfactant having the formula (I) or (II):

$$R_3$$
 R_4
 R_5
 R_6
 R_7
 R_8
 R_9
 R_9

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wherein R_1 and R_4 are a straight or a branched alkyl chain having from 3 to 10 carbon atoms; R_2 and R_3 are either H or an alkyl chain having from 1 to 5 carbon atoms; and m, n, p, and q are numbers that range from 0 to 20.

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- 20. The process solution of claim 19 wherein the process solution further comprises from about 10 to about 10,000 ppm of at least one dispersant.
- 21. The process solution of claim 20 wherein the at least one dispersant comprises an ionic compound.
- The process solution of claim 20 wherein the at least one dispersant
 comprises an nonionic compound.
 - 23. The process solution of claim 19 wherein the value of (n + m) ranges from 0 to 30.

- 24. The process solution of claim 23 wherein the value of (n + m) ranges from 1.3 to 15.
- 25. The process solution of claim 19 wherein the value of (p + q) ranges from 0 to 30.
- 5 26. The process solution of claim 25 wherein the value of (p + q) ranges from 1 to 10.
 - 27. A pre-development rinse comprising the process solution of claim 19.
 - 28. A process solution, the solution comprising:

a solvent selected from the group consisting of an aqueous solvent, a non-aqueous solvent, and combinations thereof; and

about 10 to about 10,000 ppm of at least one surfactant having the formula:

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wherein R₁ and R₄ are a straight or a branched alkyl chain having from 3 to 10 carbon atoms; R₂ and R₃ are either H or an alkyl chain having from 1 to 5 carbon atoms; and m, n, p, and q are numbers that range from 0 to 20.

- 29. A method for improving the wettability of an aqueous developer solution on a surface of a resist-coated substrate, the method comprising:
- 20 providing a process solution comprising: a solvent selected from the group consisting of an aqueous solvent, a non-aqueous solvent, and combinations thereof; and

about 10 ppm to about 10,000 ppm of at least one surfactant having the formula (I) or (II):

wherein R_1 and R_4 are a straight or a branched alkyl chain having from 3 to 10 carbon atoms; R_2 and R_3 are either H or an alkyl chain having from 1 to 5 carbon atoms; and m, n, p, and q are numbers that range from 0 to 20;

contacting the resist-coated substrate with the aqueous solution; and applying the aqueous developer solution to the resist-coated substrate wherein the contacting step is conducted prior and/or during at least a portion of the applying step.